

Features

- Frequency: 0.7GHz~2.6GHz
- Gain: 20dB
- Output P_{1dB} : 20.5dBm
- Supply Voltage: +5V@70mA
- Die Size: 1.0mm×1.25mm×0.1mm

Typical Applications

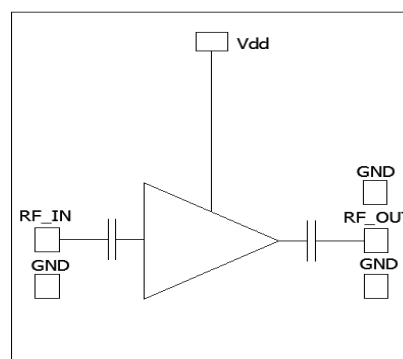
- Radar and ECM
- RF/ Microwave radio
- Military and Space
- Test and Measurement
- Fiber Optics

General Description

XT3009 is a GaAs MMIC low noise amplifier die which operates between 0.7GHz~2.6GHz. The amplifier can provide 20dB gain, 20.5dBm Output P_{1dB} and 1.3dB noise figure from 70 mA supply current.

The chip offers full passivation for increased reliability and moisture protection. This amplifier is the perfect alternative to higher cost hybrid amplifiers.

Functional Diagram



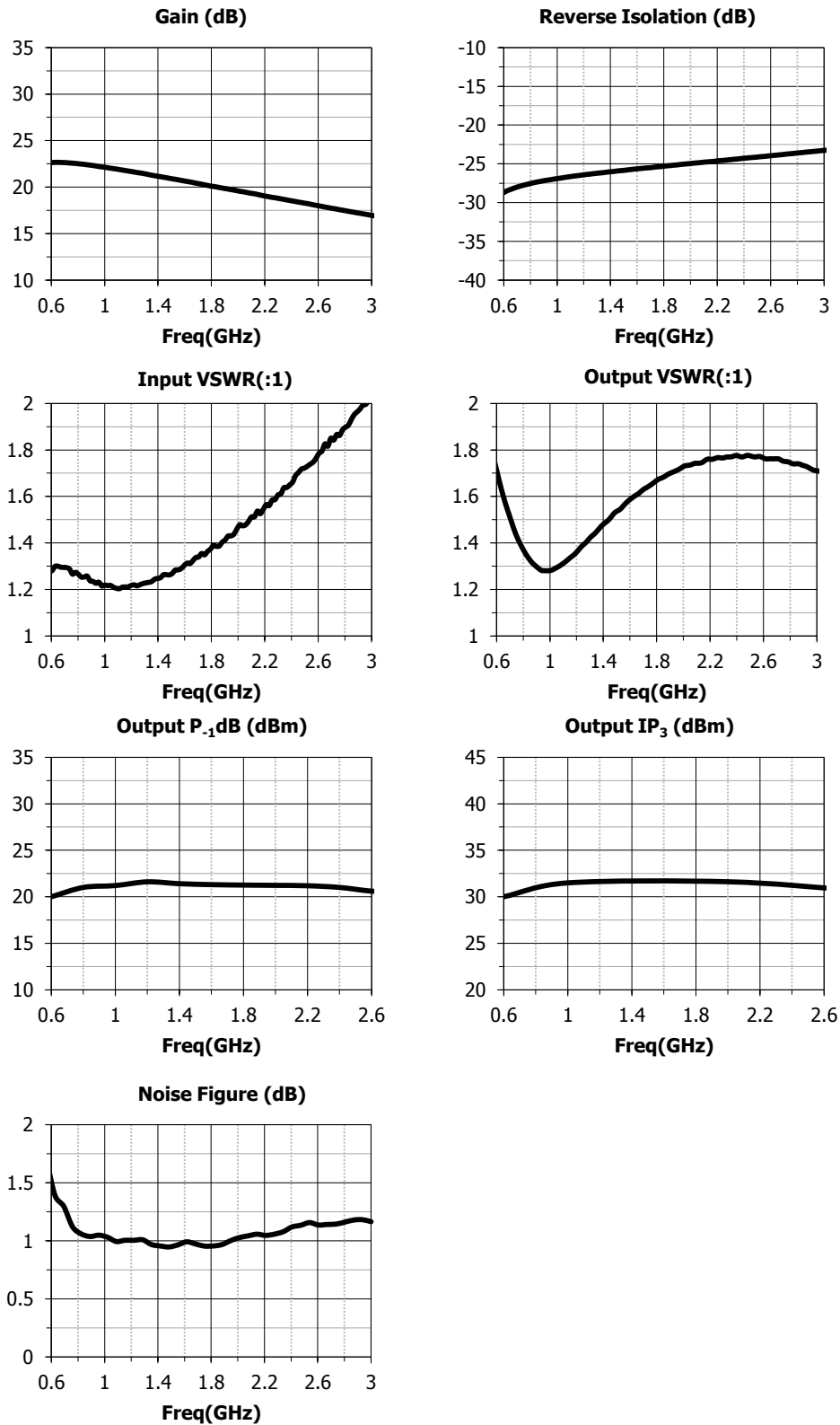
Electrical Performance ($T_A=25^{\circ}\text{C}$, $V_D=+5\text{V}$, $I_D=70\text{mA}$, $Z_0=50\Omega$)

Parameter	Min.	Typ.	Max.	Units
Frequency Range	0.7~2.6			GHz
Gain	—	20	—	dB
Gain Flatness	—	2.5	—	dB
Reverse Isolation	—	-25	—	dB
Input/Output VSWR	—	1.7	—	:1
Noise Figure	—	1.2	—	dB
Output Power for 1 dB Compression (OP_{1dB})	—	20.5	—	dBm
Output Third Order Intercept (OIP_3)	—	31	—	dBm
Supply Current(I_D)	—	70	—	mA

Absolute Maximum Ratings

Maximum Input Power	+18dBm	Operating Temperature	-55°C~+85°C
Junction Temperature	+150°C	Storage Temperature	-65°C~+150°C

Typical Performance Curve



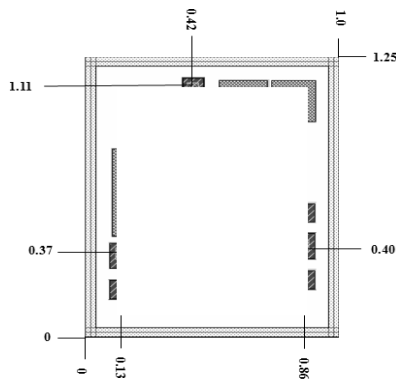
XT3009



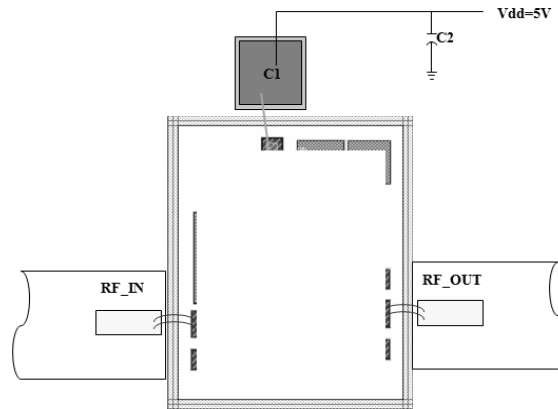
GaAs MMIC Low Noise Amplifier
0.7GHz~2.6GHz

Rev 2.0

Die Outline (all dimensions in mm)



Assembly Diagram



Components List

Reference Des.	Value	Part Number	Manuf.	Size
C1	300pF	CHIP CAPACITOR	RADVISTA	—
C2	10nF	GRM155R71H103KA88D	MURATA	0402

Attention:

GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.